

Key Features

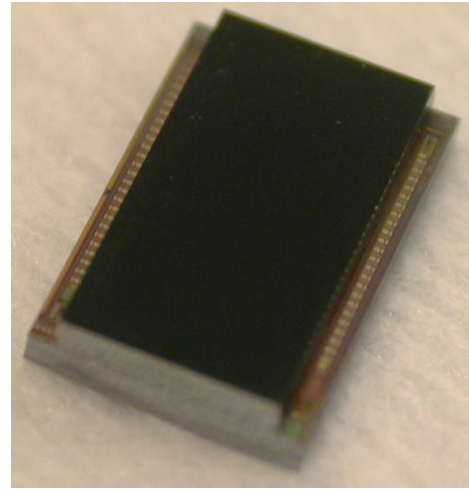
80x80 FPA size

35 μ m detector pitch

Wafer-level vacuum packaged

Easy-to-use 3-wire SPI programming interface

Ultra low-cost CMOS infrared (CIR) microbolometer technology
Patent granted



Technical Specifications

Detector Technology	CMOS Infrared (CIR) Microbolometer
Wavelength	7.5 μ m – 13.5 μ m (LWIR)
FPA Size	80 x 80
Detector Pitch	35 μ m
NETD	< 250 mK @ 17 fps with F/1 optics < 110 mK @ 4 fps with F/1 optics
Electrical Power Dissipation	< 20 mW 3.3V analog, 1.8V digital power supply
Frame Rate	Up to 30 fps, programmable
Readout Mode	Rolling line
Readout Gain	Programmable
Video Output	Pseudo-differential analog output, 2.0V swing
Sensor Programming Interface	3-wire SPI
Video Synchronization	Master mode with self trigger, slave mode with external sync signal
Physical Dimensions	8" CMOS wafers, 5.41mm x 6.48mm die dimensions
Availability	Tested dies and wafers will be available as engineering samples @ Q2/2017
Engineering Characterization Platform	Testing platform (electronics, firmware, software, and SDK) will be available @ Q1/2017